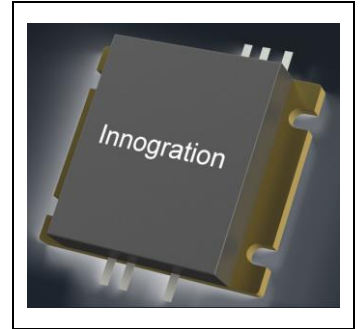




1.2-1.4GHz, 200W , 2 stages GaN Fully matched PA

Description

The S2MBV1214-200H3P is a 200-watt Psat capable, 2 stage integrated IMFET, designed for L band applications, with frequencies from 1.2 to 1.4GHz. The module is 50 Ω input/output matched and requires minimal external components, with DC block capacitor integrated inside. The module implements multiple GaN active dice and its matching network within highly compact 30.8*27.4mm metal RF package with excellent capability for heat dissipation.



| VDS= 50V, Vgs1= -3.32V, Idq1=230mA, Vgs2= -3.2V, Idq2=20mA | | | | | | | |
|--|------------|----------|--------------|----------------|------------|----------|--------------|
| Freq (MHz) | P1dB (dBm) | P1dB (W) | P1dB Eff (%) | P1dB Gain (dB) | P3dB (dBm) | P3dB (W) | P3dB Eff (%) |
| 1200 | 52.62 | 182.8 | 49.9 | 31.57 | 53.86 | 243.1 | 55.6 |
| 1250 | 52.56 | 180.5 | 51.6 | 32.27 | 53.89 | 244.9 | 57.8 |
| 1300 | 52.76 | 188.9 | 55.0 | 31.84 | 54.12 | 258.1 | 61.4 |
| 1350 | 52.92 | 196.1 | 57.7 | 31.82 | 54.2 | 262.8 | 63.5 |
| 1400 | 52.72 | 187.2 | 58.5 | 31.32 | 54.06 | 254.5 | 64.3 |

Applications

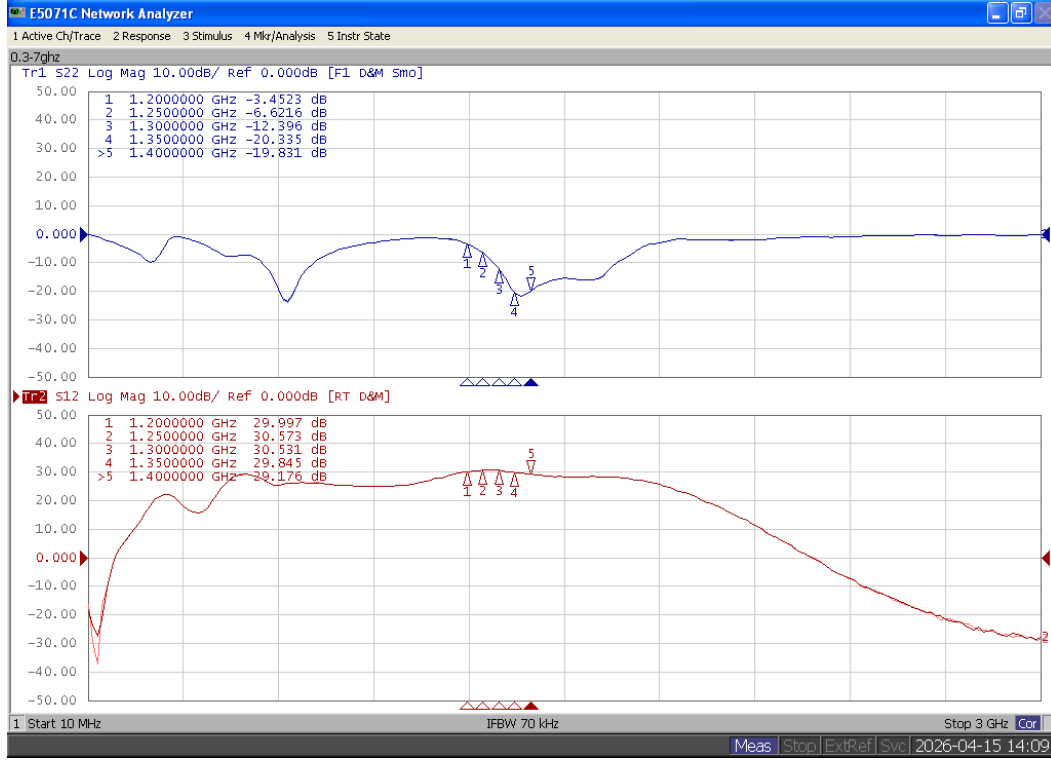
- L band power amplifier

Table 1. Maximum Ratings

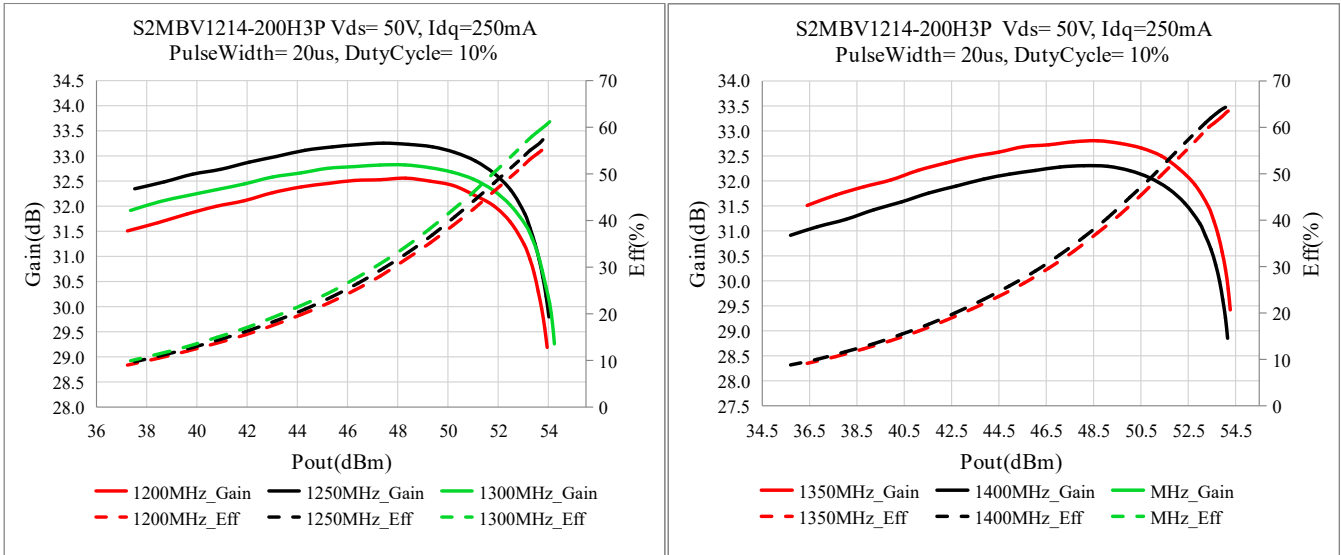
| Rating | Symbol | Value | Unit |
|--------------------------------|------------------|-------------|------|
| Drain--Source Voltage | V _{DSS} | 200 | Vdc |
| Gate--Source Voltage | V _{GS} | -10 to +2 | Vdc |
| Operating Voltage | V _{DD} | +55 | Vdc |
| Storage Temperature Range | T _{stg} | -65 to +150 | °C |
| Case Operating Temperature | T _c | +150 | °C |
| Operating Junction Temperature | T _j | +225 | °C |

TYPICAL CHARACTERISTICS

Figure 1. Network analyzer output S11/S21 (Pin=0dBm, Idq=200mA)



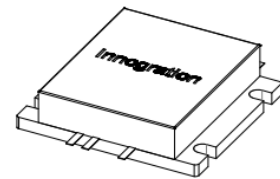
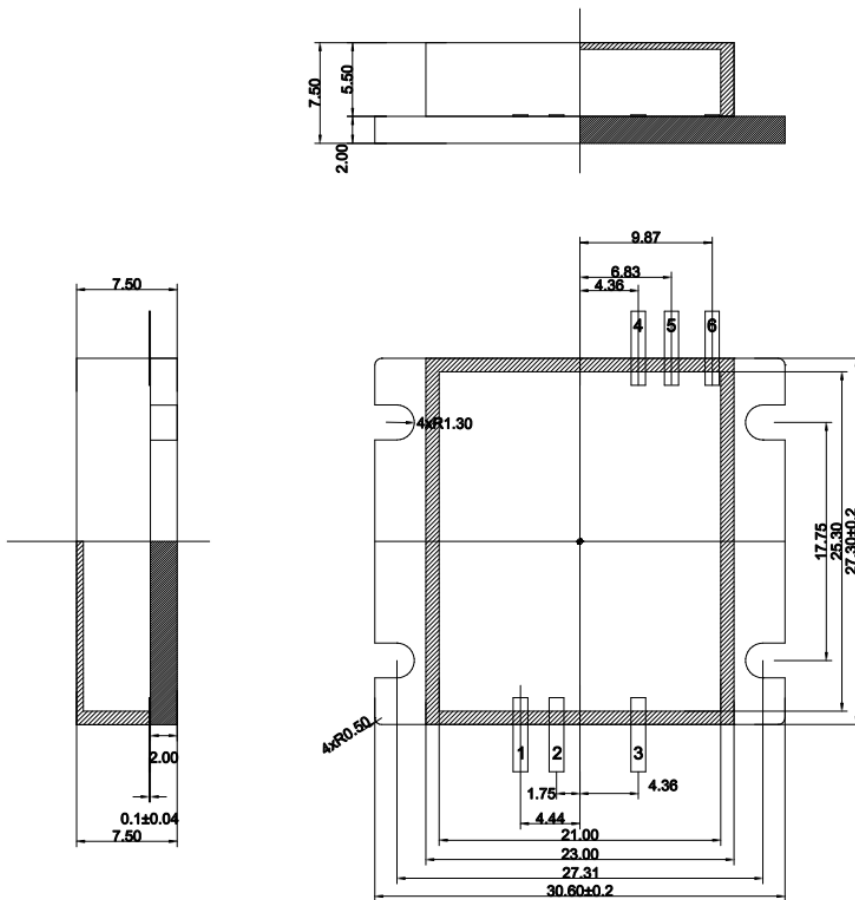
1 Figure 3. Pout, Eff, Gain, drain current Vs Frequency @50V ,Pulsed 20us 20%



Typical application board



Package Dimensions (Unit:mm)



| Pin definition | | | | | |
|----------------|------|------|-------|------|------|
| 1 | 2 | 3 | 4 | 5 | 6 |
| Vgs1 | Vgs2 | RFin | RFout | Vds1 | Vds2 |



Revision history

Table 6. Document revision history

| Date | Revision | Datasheet Status |
|-----------|----------|--------------------|
| 2026/4/15 | Rev 1.0 | Advanced Datasheet |
| | | |
| | | |

Application data based on LBG-26-18

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